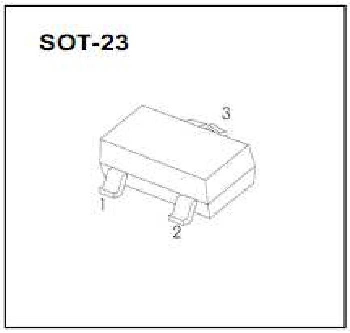
SLS SEMICONDUCTOR (SHENZHEN) CO.,LTD.

SOT-23 封装半导体二极管/SOT-23 Plastic-Encapsulate Diodes

BAW56&BAV70&BAV99

(SWITCHING DIODES)



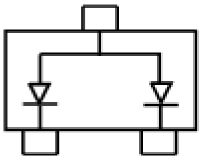
特点/Features:

速度快;

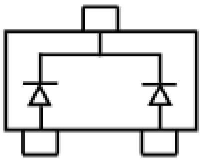
用途/Applications:

高速开关电路。

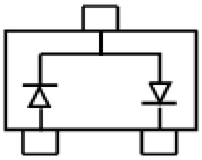
电路和印章/Circuit&Marking:



BAW56 Marking: A1



BAV70 Marking: A4



BAV99 Marking: A7

极限参数/Absolute maximum ratings(Ta=25℃)

参数/Parameter	符号/ Symbol	数值/Value	单位/Unit
反向电压/Reverse Voltage	V_R	70	V
正向电流/Forward Current	I_F	200	mA
正向瞬间峰值电流/Peak Forward Surge Current	$I_{FM(surge)}$	500	mA
功率/ Power Dissipation	P_D	0.225	W
热阻/Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	556	℃/W
结温/Junction Temperature	Tj	150	℃
储存温度/Storage Temperature	Tstg	-55～150	℃

电性能参数/Electrical characteristics (Ta=25℃)

参数/Parsmeter	符号	测试条件	最小值	最大值	单位
反向击穿电压/Reverse Breakdown Voltage	V_R	I_R=100μA	70		V
正向电压/Forward Voltage	V_{F1}	I_F=1mA		0.715	V
	V_{F2}	I_F=10mA		0.855	V
	V_{F3}	I_F=50mA		1	μA
	V_{F4}	I_F=150mA		1.25	μA
反向漏电流/Reverse Current	I_R	V_R=70V		2.5	μA
端电容/Capacitance Between Terminals	C_T	V_R=0, f=1MHz		1.5	pF
反向恢复时间/Reverse Recovery Time	t_{rr}	$I_F=I_R$=10mA, Irr=0.1×I_R, R_L=100Ω		6	nS

典型特性曲线图/Typical Characteristics

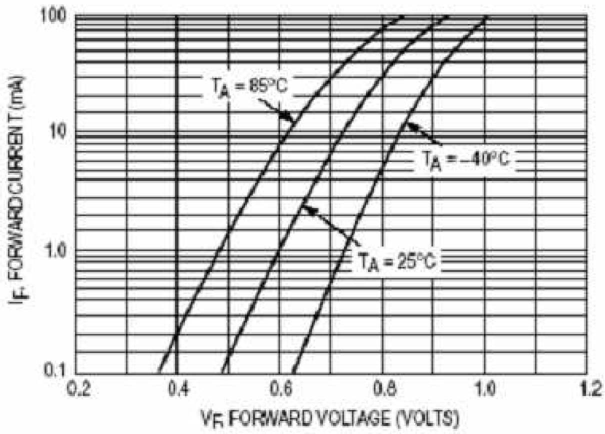


Figure 1. Forward Voltage

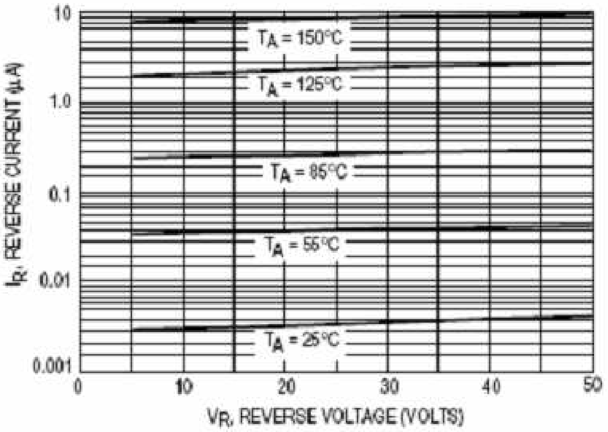


Figure 2 Leakage Current

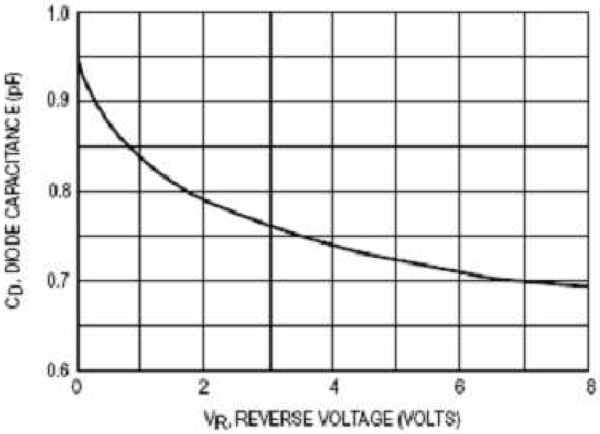


Figure 3 Capacitance